



DMP2035U

P-CHANNEL ENHANCEMENT MODE MOSFET

Features

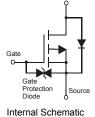
- Low On-Resistance
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- Lead Free By Design/RoHS Compliant (Note 1)
- ESD Protected Up To 3KV
- "Green" Device (Note 2)
- Qualified to AEC-Q101 Standards for High Reliability

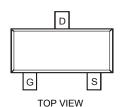
Mechanical Data

- Case: SOT-23
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020D
- Terminal Connections: See Diagram Below
- Marking Information: See Page 4
- Ordering Information: See Page 4
- Weight: 0.008 grams (approximate)









TOP VIEW

 $\begin{tabular}{ll} \textbf{Maximum Ratings} $_@T_A = 25^{\circ}C$ unless otherwise specified \\ \end{tabular}$

| Characterist | С | | Symbol | Value | Unit |
|---|---|------------------|--------------|-------|------|
| Drain-Source Voltage | | | V_{DSS} | -20 | V |
| Gate-Source Voltage | | V _{GSS} | ±8 | V | |
| Continuous Drain Current (Note 3) Steady $T_A = 25^{\circ}C$ State $T_A = 70^{\circ}C$ | | I _D | -3.6 -2.9 | Α | |
| Pulsed Drain Current (Note 4) | | I _{DM} | -24 | Α | |

Thermal Characteristics

| Characteristic | Symbol | Value | Unit |
|--|-----------------------------------|-------------|------|
| Power Dissipation (Note 3) | P_{D} | 0.81 | W |
| Thermal Resistance, Junction to Ambient @T _A = 25°C | $R_{\theta JA}$ | 153.5 | °C/W |
| Operating and Storage Temperature Range | T _J , T _{STG} | -55 to +150 | °C |

Notes:

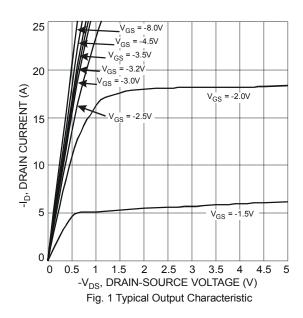
- 1. No purposefully added lead.
- 2. Diodes Inc.'s "Green" policy can be found on our website at http://www.diodes.com/products/lead_free/index.php.
 3. Device mounted on FR-4 PCB with 2 oz. Copper and test pulse width t ≦10s.
- 4. Repetitive rating, pulse width limited by junction temperature.

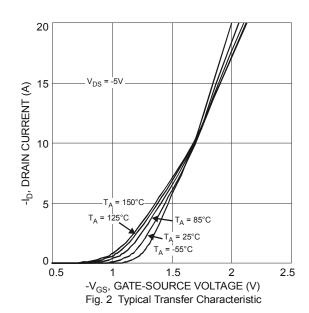


Electrical Characteristics @TA = 25°C unless otherwise specified

| Characteristic | Symbol | Min | Тур | Max | Unit | Test Condition | | |
|---|---------------------|------|----------------|----------------|----------|--|--|--|
| OFF CHARACTERISTICS (Note 5) | | | | | | | | |
| Drain-Source Breakdown Voltage | BV _{DSS} | -20 | - | - | V | $V_{GS} = 0V, I_D = -250\mu A$ | | |
| Zero Gate Voltage Drain Current T _J = 25°C | I _{DSS} | 1 | - | -1.0 | μ A | $V_{DS} = -20V, V_{GS} = 0V$ | | |
| Gate-Source Leakage | IGSS | 1 | - | ±10 | μ A | $V_{GS} = \pm 8V$, $V_{DS} = 0V$ | | |
| ON CHARACTERISTICS (Note 5) | | | | | | | | |
| Gate Threshold Voltage | $V_{GS(th)}$ | -0.4 | -0.7 | -1.0 | ٧ | $V_{DS} = V_{GS}, I_{D} = -250 \mu A$ | | |
| | | | 23 30 41 | 35 45 62 | | $V_{GS} = -4.5V$, $I_D = -4.0A$ | | |
| Static Drain-Source On-Resistance | R _{DS(ON)} | - | | | mΩ | $V_{GS} = -2.5V$, $I_D = -4.0A$ | | |
| | | | | | | $V_{GS} = -1.8V$, $I_D = -2.0A$ | | |
| Forward Transfer Admittance | Y _{fs} | - | 14 | - | S | $V_{DS} = -5V, I_{D} = -4A$ | | |
| Diode Forward Voltage | V_{SD} | - | -0.7 | -1.0 | V | $V_{GS} = 0V, I_{S} = -1A$ | | |
| DYNAMIC CHARACTERISTICS | | | - | - | | | | |
| Input Capacitance | C _{iss} | ı | 1610 | - | рF | 1/ 401/1/ 01/ | | |
| Output Capacitance | Coss | - | 157 | - | pF | V _{DS} =-10V, V _{GS} = 0V -f = 1.0MHz | | |
| Reverse Transfer Capacitance | C _{rss} | - | 145 | - | pF | 1 - 1.001112 | | |
| Gate Resistance | R_g | - | 9.45 | - | Ω | V_{DS} =0V, V_{GS} = 0V, f = 1MHz | | |
| Total Gate Charge | Q_g | - | 15.4 | - | nC | \\ - 45\\ \\ - 40\\ | | |
| Gate-Source Charge | Q_{gs} | - | 2.5 | - | nC | $V_{GS} = -4.5V$, $V_{DS} = -10V$, | | |
| Gate-Drain Charge | Q_{gd} | - | 3.3 | - | nC | -I _D =-4A | | |
| Turn-On Delay Time | t _{D(on)} | - | 16.8 | - | ns | | | |
| Turn-On Rise Time | t _r | - | 12.4 | - | ns | $V_{DS} = -10V, V_{GS} = -4.5V,$ | | |
| Turn-Off Delay Time | t _{D(off)} | - | 94.1 | - | ns | $R_L = 10\Omega$, $R_G = 6.0\Omega$, $I_D = -1A$ | | |
| Turn-Off Fall Time | t _f | - | 42.4 | - | ns | | | |

Notes: 5. Short duration pulse test used to minimize self-heating effect.





T_A = 150°C T_A = 125°C

T_A = 85°C

T_Δ = 25°C

Γ_A = -55°C

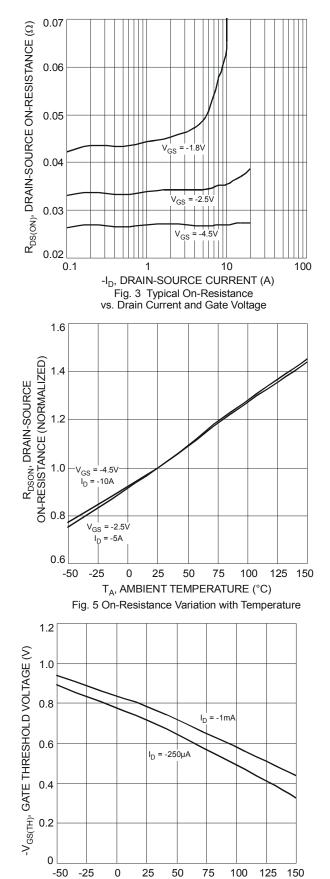
20

16

100

125 150





T_A, AMBIENT TEMPERATURE (°C)

Fig. 7 Gate Threshold Variation vs. Ambient Temperature

 $R_{DS(ON)}$, DRAIN-SOURCE ON-RESISTANCE (Ω) 0.01 8 12 -I_D, DRAIN CURRENT (A) 0 Fig. 4 Typical On-Resistance vs. Drain Current and Temperature 0.06 R_{DSON} , DRAIN-SOURCE ON-RESISTANCE (Ω) 0.05 0.04 V_{GS} = -2.5V $I_D = -5A$ 0.03 0.02 = -10A 0.01 -50 -25 0 25 50 75 T_A, AMBIENT TEMPERATURE (°C) Fig. 6 On-Resistance Variation with Temperature 20 18 16 -I_S, SOURCE CURRENT (A) 14 12 6 2 0 0 0.6 0.9 -V_{SD}, SOURCE-DRAIN VOLTAGE (V) Fig. 8 Diode Forward Voltage vs. Current

0.05

0.04

0.03

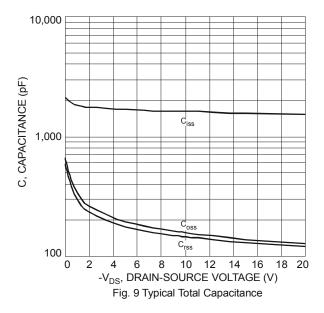
0.02

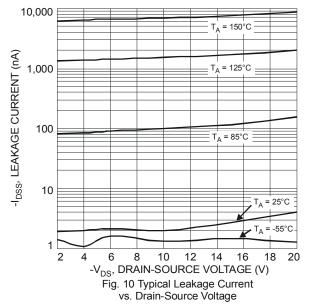
-4.5V V_{GS}

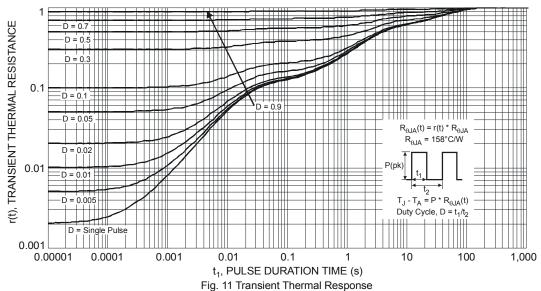
1.5

1.2







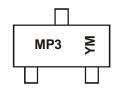


Ordering Information (Note 6)

| Part Number | Case | Packaging | | |
|-------------|--------|-----------------------|--|--|
| DMP2035U-7 | SOT-23 | 3000 / 7" Tape & Reel | | |

Notes: 6. For packaging details, go to our website at http://www.diodes.com/datasheets/ap02007.pdf.

Marking Information



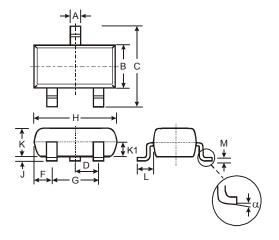
MP3 = Product Type Marking Code YM = Date Code Marking Y = Year (ex: W = 2009) M = Month (ex: 9 = September)

Date Code Key

| Year | 2009 | 9 | 2010 | | 2011 | 20 | 12 | 2013 | | 2014 | - 2 | 2015 |
|-------|------|-----|------|-----|------|-----|-----|------|-----|------|-----|------|
| Code | W | | X | | Υ | 1 | 7 | Α | | В | | С |
| Month | Jan | Feb | Mar | Apr | May | Jun | Jul | Aug | Sep | Oct | Nov | Dec |
| Code | 1 | 2 | 3 | 4 | 5 | 6 | 7 | 8 | 9 | 0 | N | D |

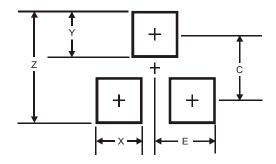


Package Outline Dimensions



| | SOT-23 | | | | | | |
|-----|----------------------|------|-------|--|--|--|--|
| Dim | Min | Max | Тур | | | | |
| Α | 0.37 | 0.51 | 0.40 | | | | |
| В | 1.20 | 1.40 | 1.30 | | | | |
| С | 2.30 | 2.50 | 2.40 | | | | |
| D | 0.89 | 1.03 | 0.915 | | | | |
| F | 0.45 | 0.60 | 0.535 | | | | |
| G | 1.78 | 2.05 | 1.83 | | | | |
| Н | 2.80 | 3.00 | 2.90 | | | | |
| J | 0.013 | 0.10 | 0.05 | | | | |
| K | 0.903 | 1.10 | 1.00 | | | | |
| K1 | - | 1 | 0.400 | | | | |
| L | 0.45 | 0.61 | 0.55 | | | | |
| M | 0.085 | 0.18 | 0.11 | | | | |
| α | 0° | 8° | - | | | | |
| All | All Dimensions in mm | | | | | | |

Suggested Pad Layout



| Dimensions | Value (in mm) |
|------------|---------------|
| Z | 2.9 |
| Х | 0.8 |
| Υ | 0.9 |
| С | 2.0 |
| ш | 1 35 |



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